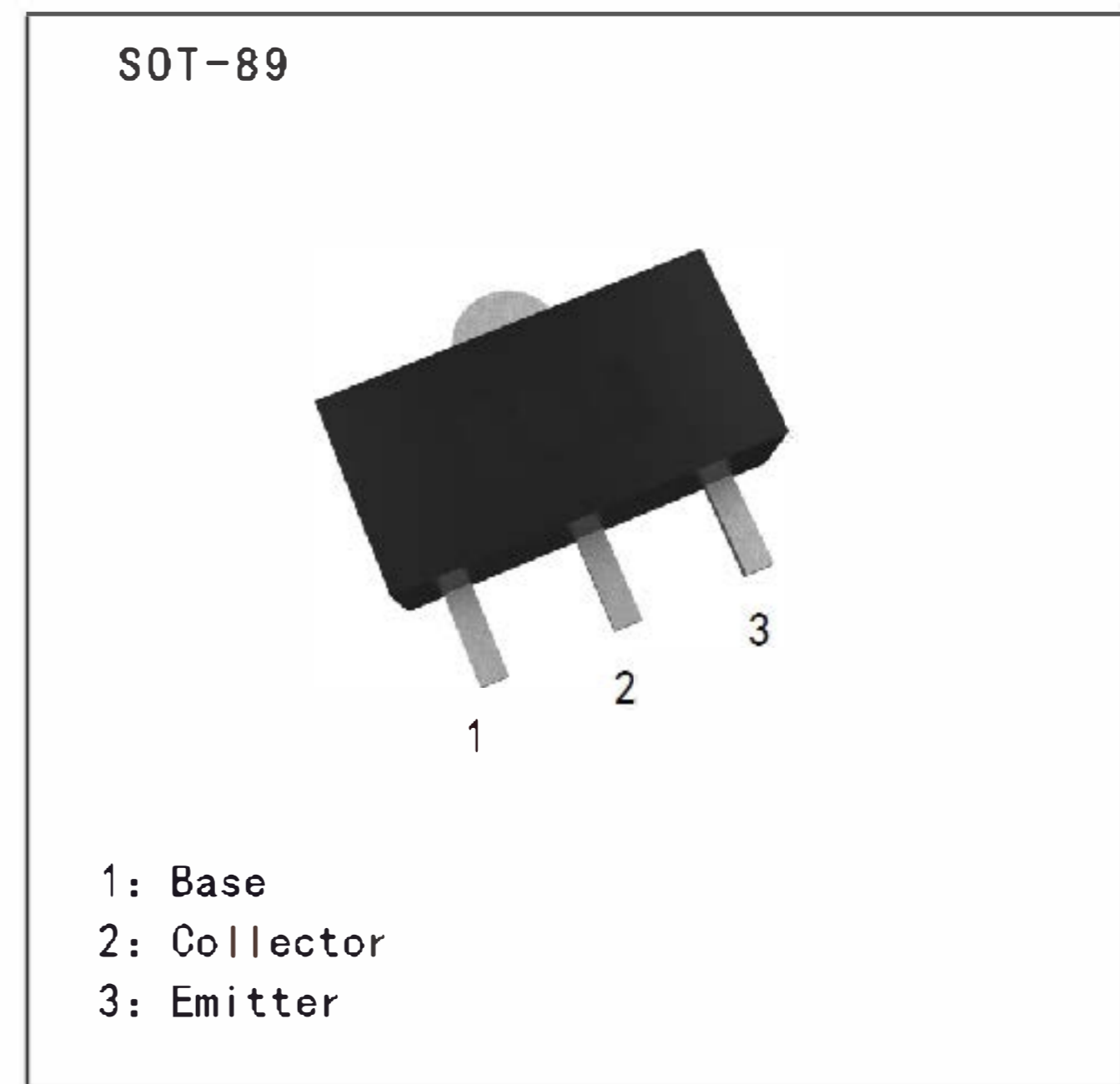


● Features

High collector to emitter voltage: $V_{CE0} > -120V$.



● Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-120	V
Collector-emitter voltage	V_{CE0}	-120	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-0.7	A
Collector current (pulse) *1	$I_{C(pu)}$	-1.2	A
Collector power dissipation	P_C	2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

*1. $PW \leq 10ms, duty\ cycle \leq 50\%$

● Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -120V, I_E = 0$			-100	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	nA
DC current gain *	h_{FE}	$V_{CE} = -1V, I_C = -100mA$	90	200	400	
		$V_{CE} = -1V, I_C = -5.0mA$	45	200		
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.4	-0.6	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.9	-1.5	V
Base-emitter voltage *	V_{BE}	$V_{CE} = -10V, I_C = -10mA$	-550	-620	-650	mV
Output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1.0MHz$		14		pF
Transition frequency	f_T	$V_{CE} = -10V, I_E = 10mA$		75		MHz

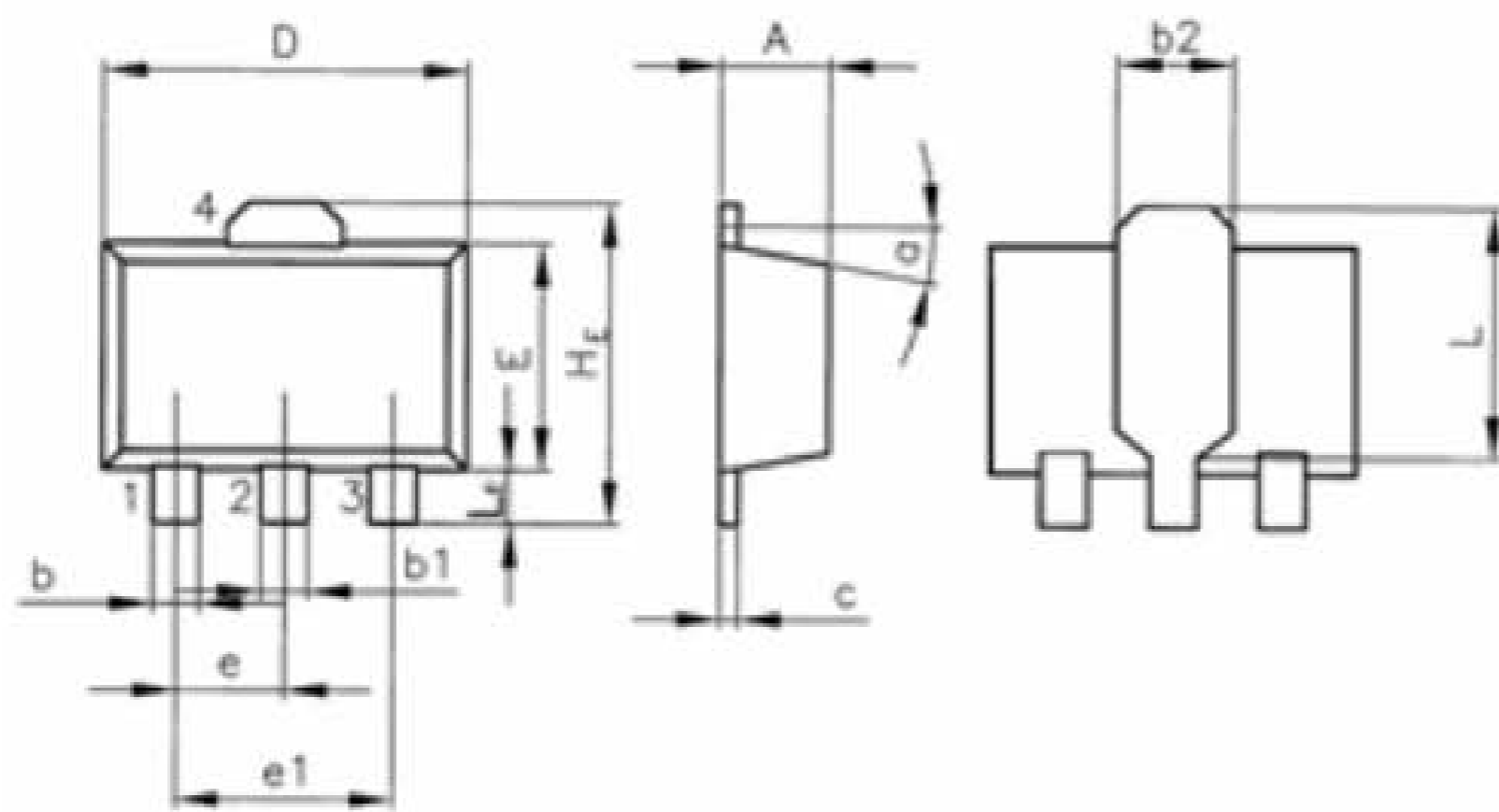
* $PW \leq 350\mu s, duty\ cycle \leq 2\%$

● h_{FE} Classification

Marking	KR	KQ	KP
h_{FE}	90~180	135~270	200~400

Outline dimensions (see fig.1)

unit: mm



dimensions symbol	SOT-89		
	min	type	max
A	1.4	—	1.6
b	0.35	—	0.55
b1	0.4	—	0.65
b2	—	1.6	—
c	0.35	—	0.45
D	4.4	—	4.6
E	2.35	—	2.55
e	—	1.5	—
e1	—	3	—
H _F	—	4.15	—
L	—	2.7	—
LE	—	1.0	—
α	—	5°	—

Fig.1 Outline dimensions

Typical curve

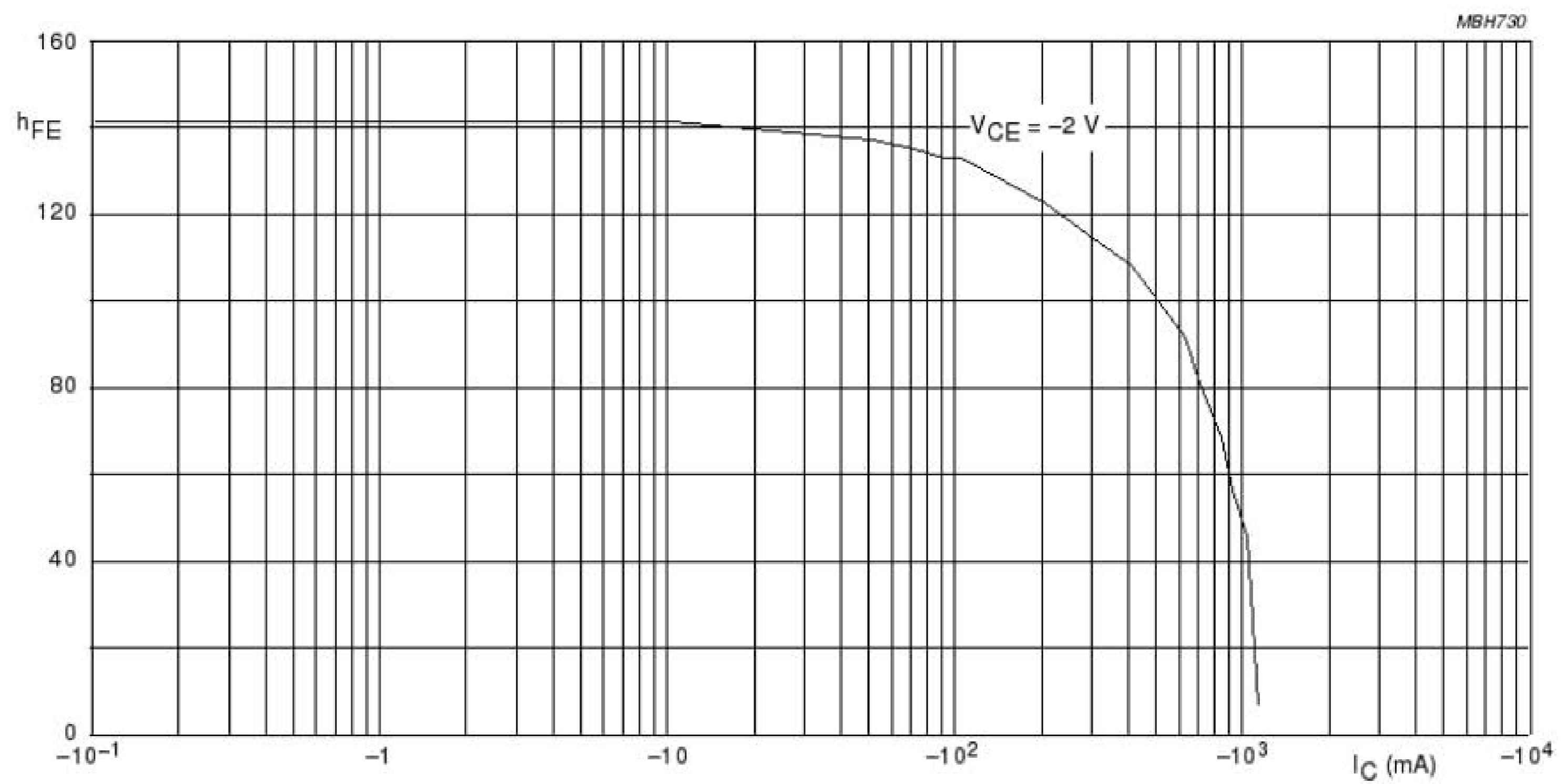


Fig.2 DC current gain; typical values.

单击下面可查看定价，库存，交付和生命周期等信息

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